

THE UNIVERSITY OF CHICAGO

FIG. 1A

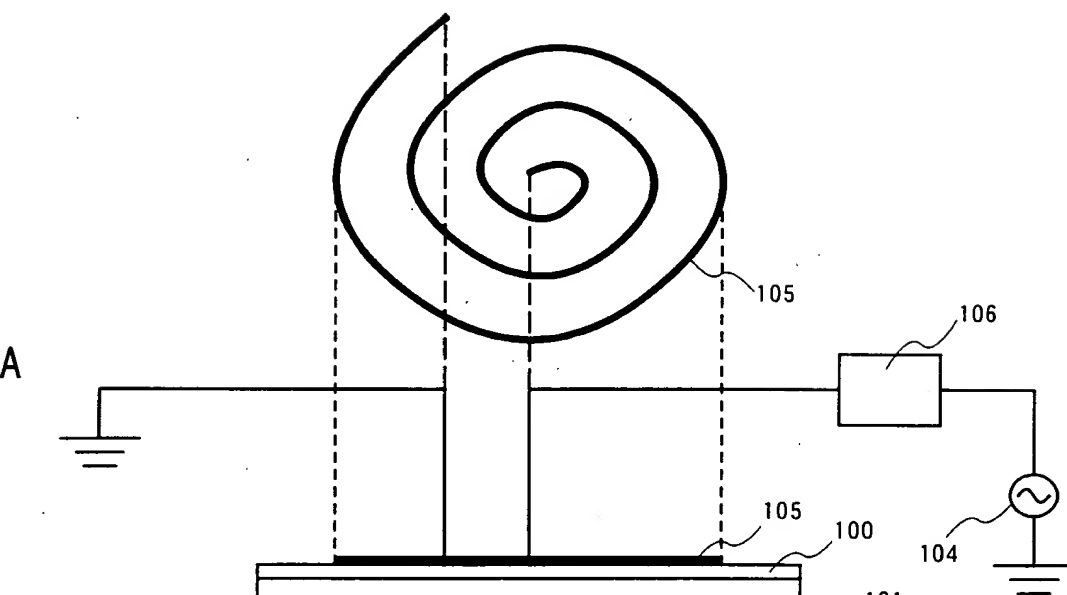


FIG. 1B

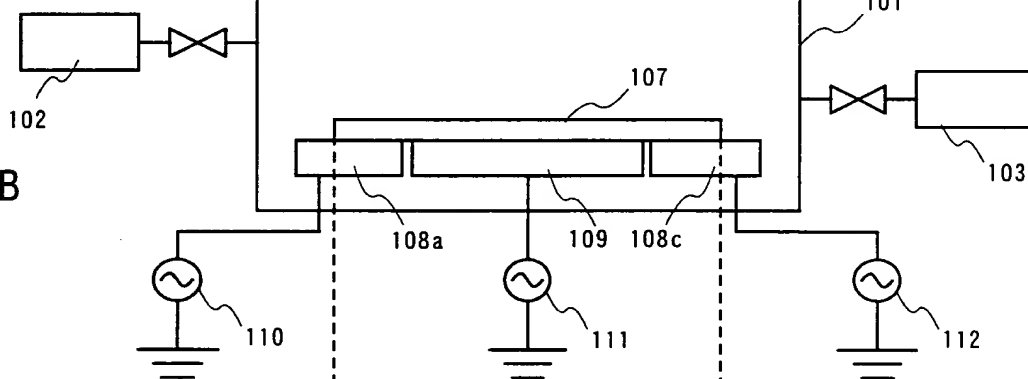


FIG. 1C

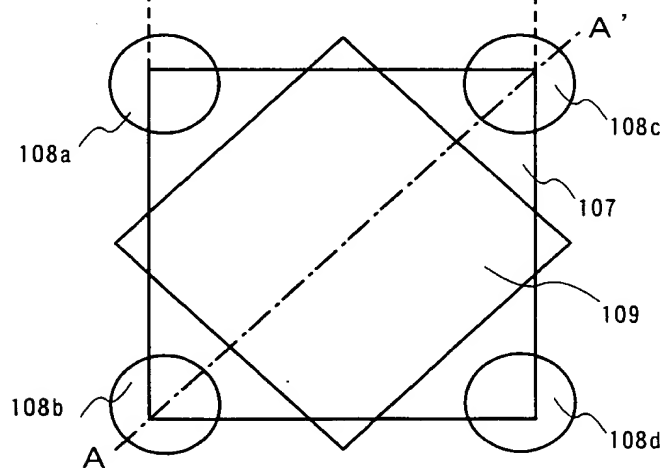


FIG. 2B

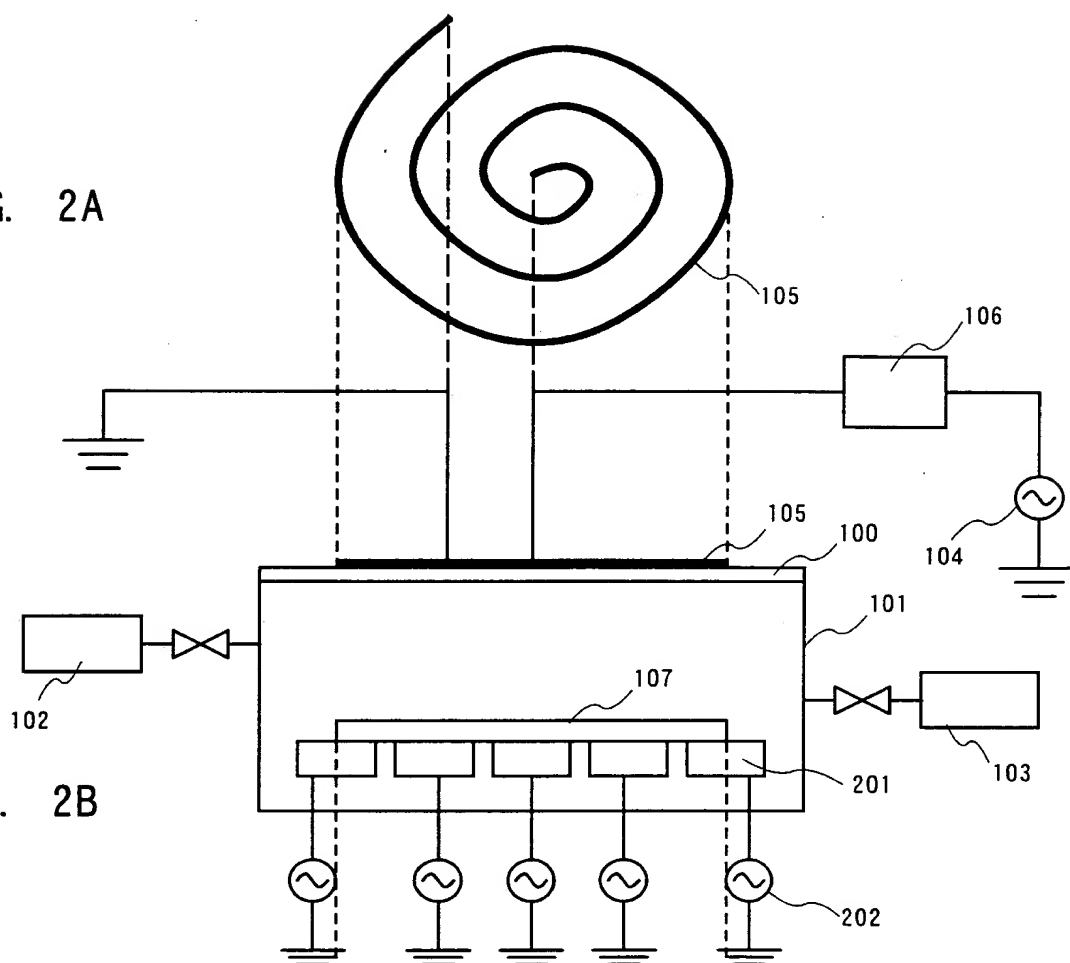


FIG. 2C

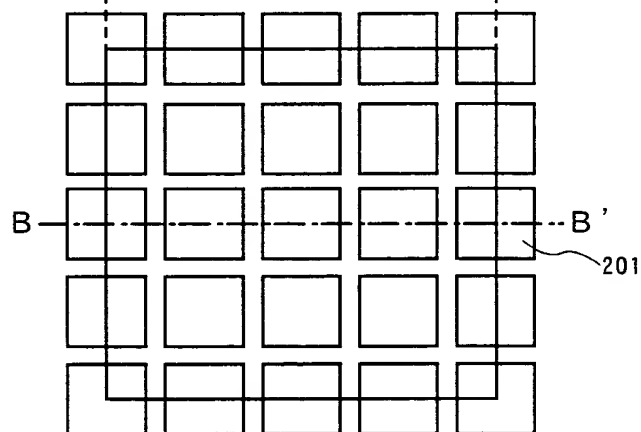


FIG. 3A

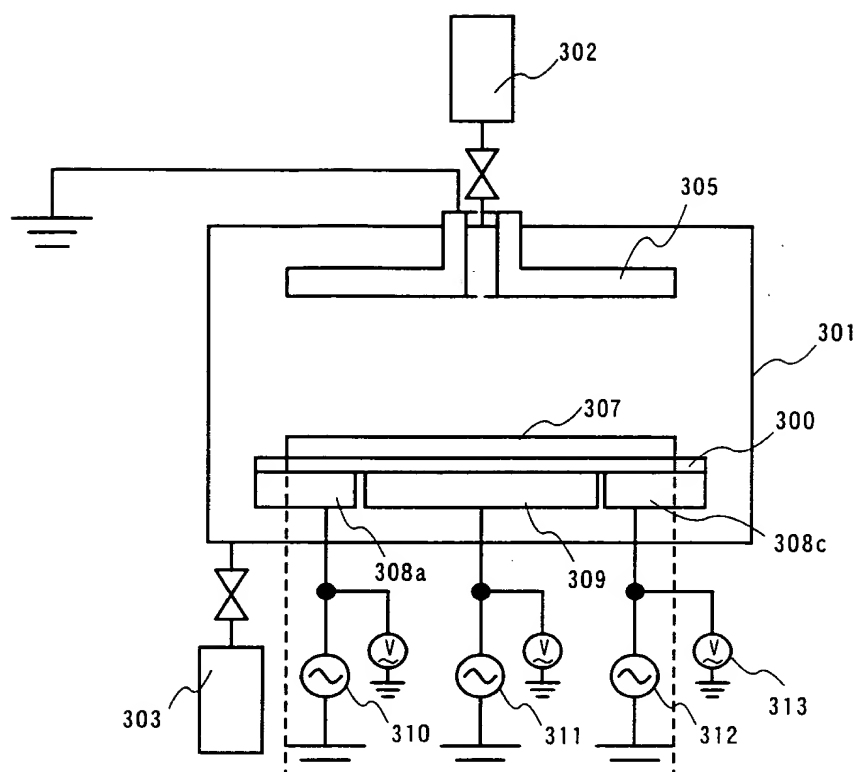
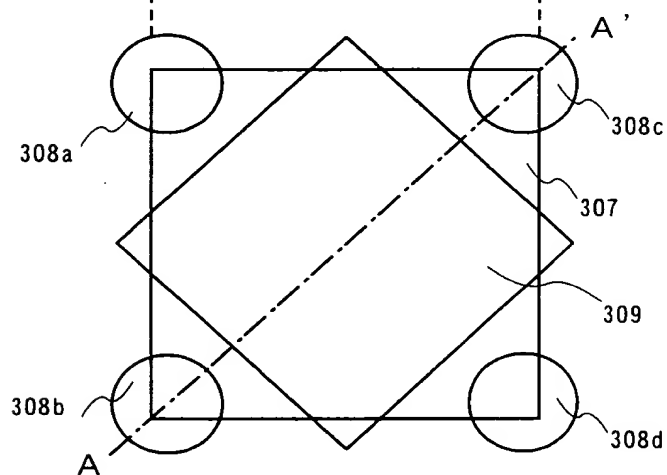


FIG. 3B



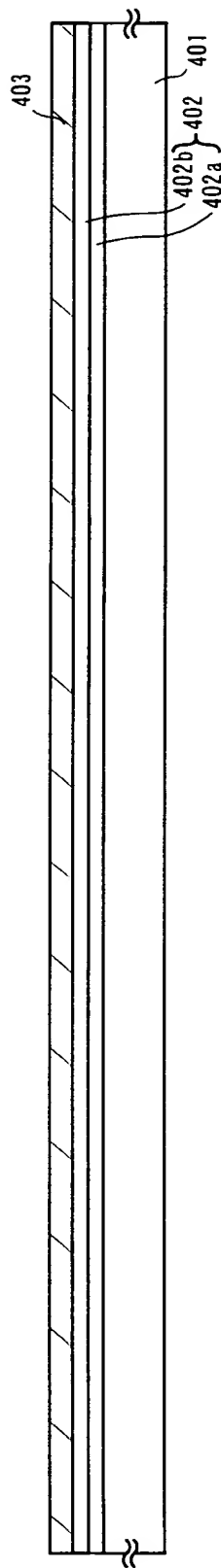


FIG. 4A



FIG. 4B

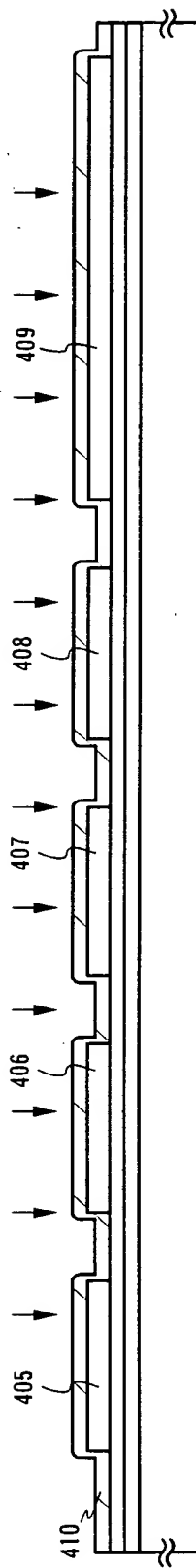


FIG. 4C

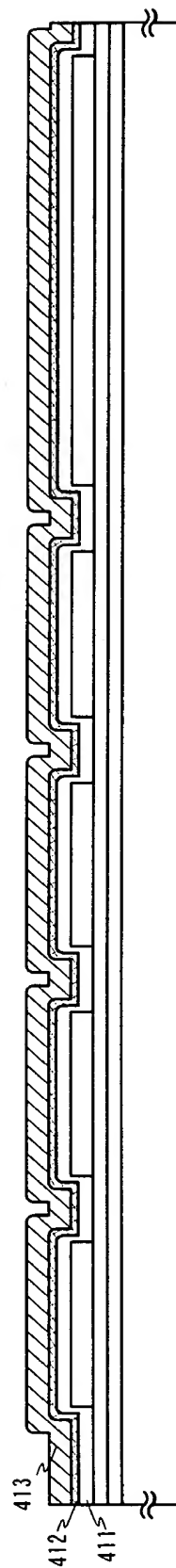


FIG. 4D

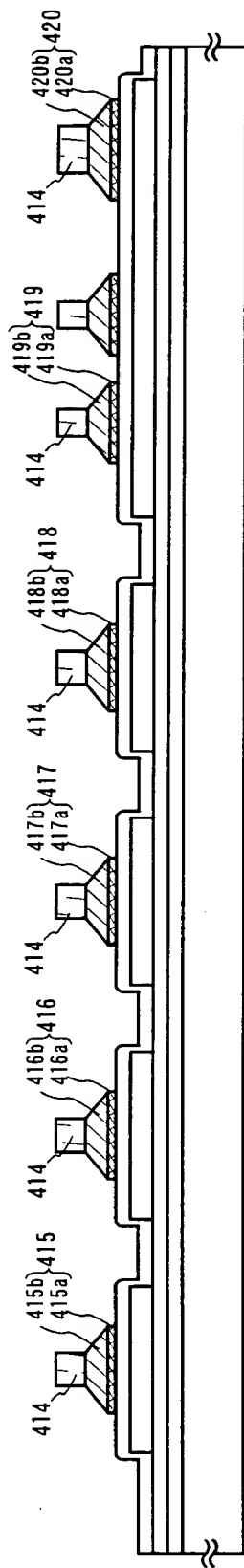


FIG. 5A

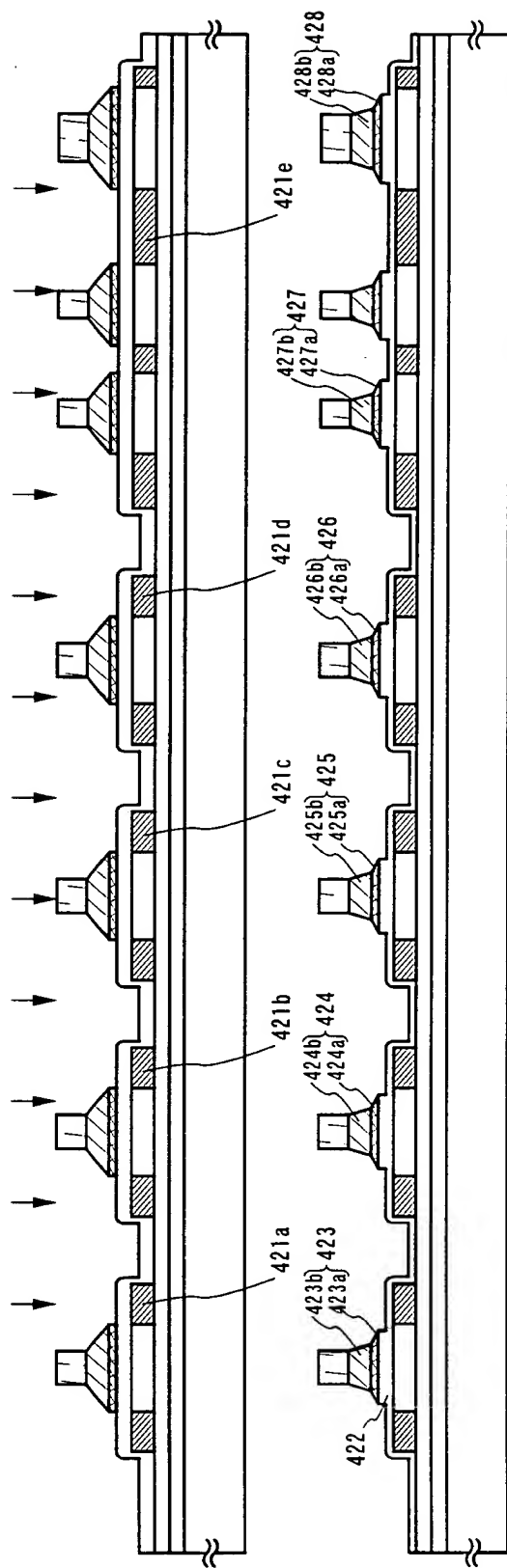


FIG. 5B

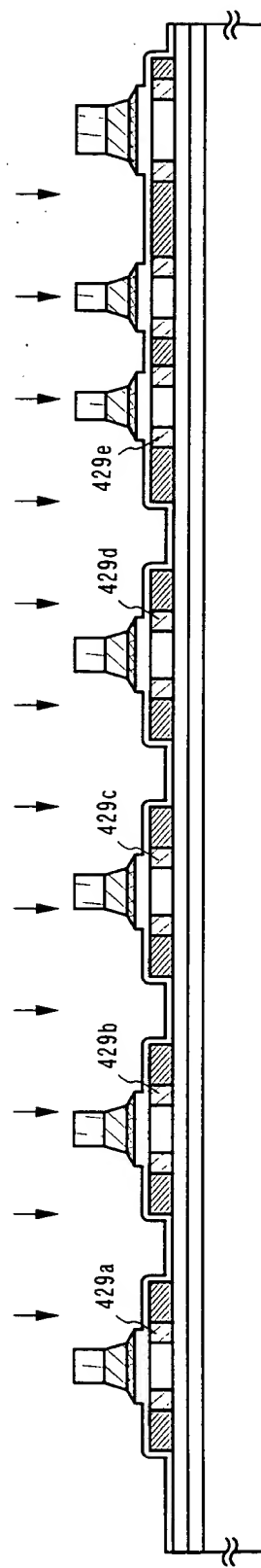


FIG. 5C

FIG. 5D

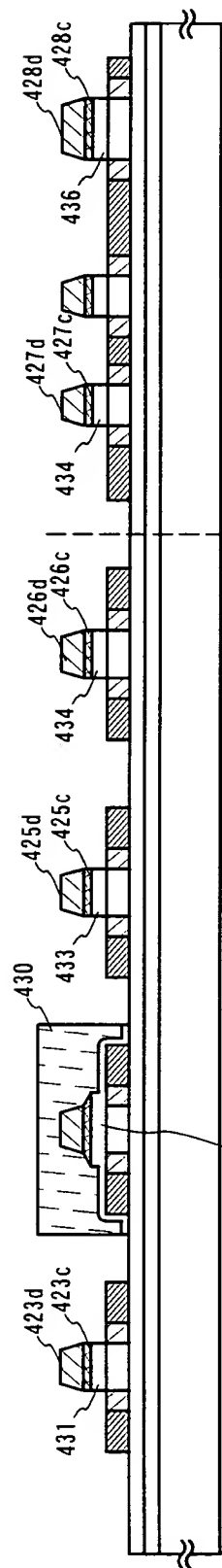


FIG. 6A

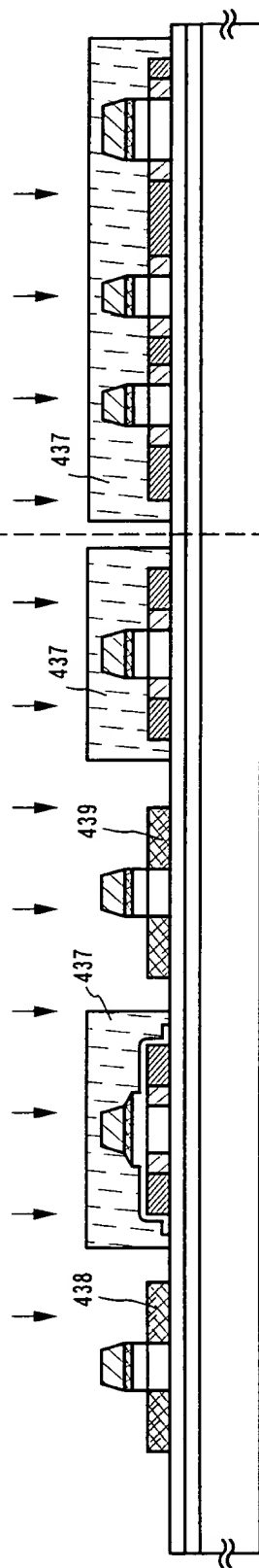


FIG. 6B

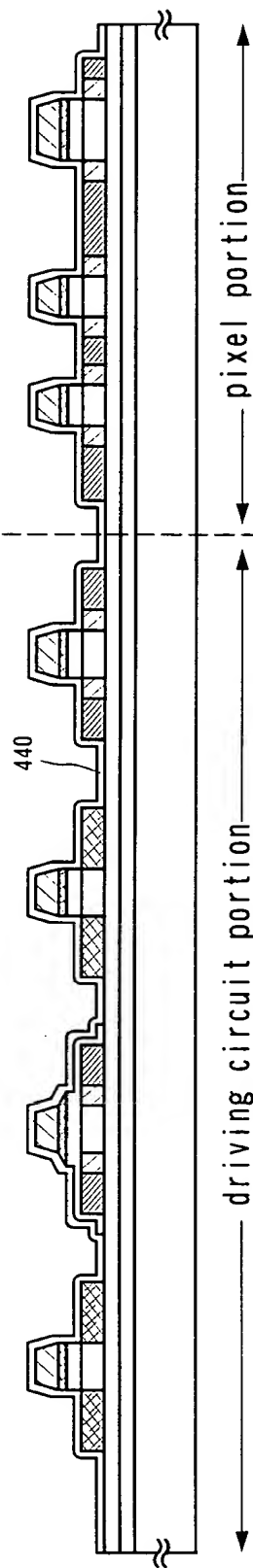


FIG. 6C

pixel portion

driving circuit portion

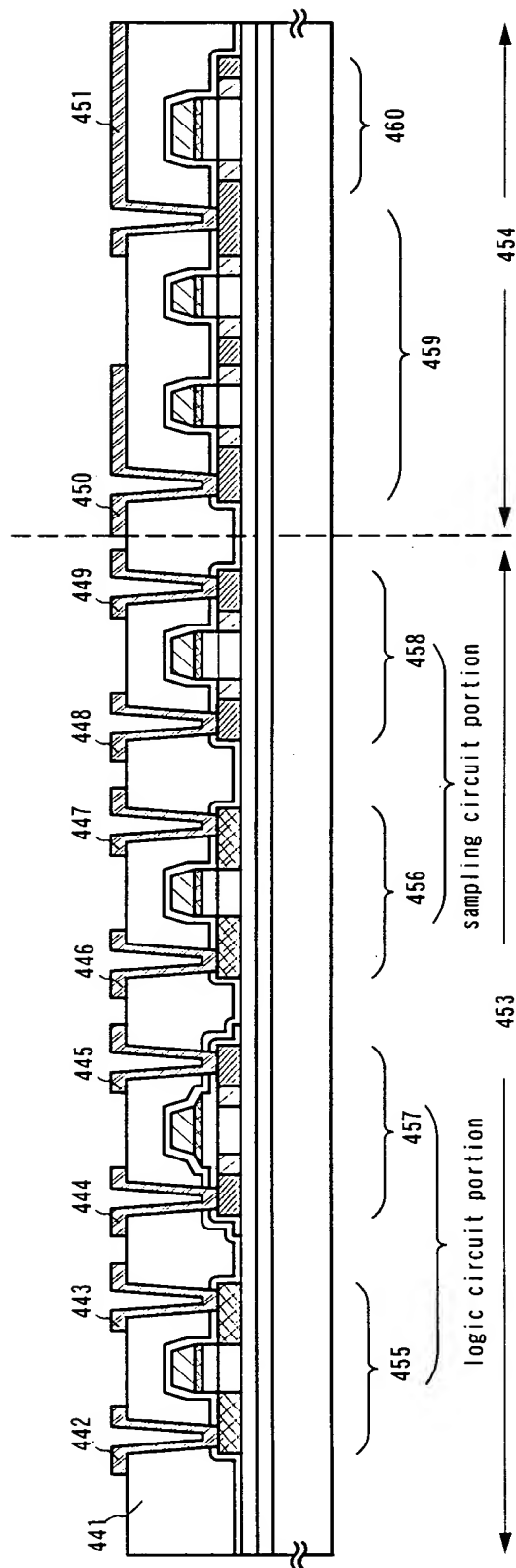


FIG. 7

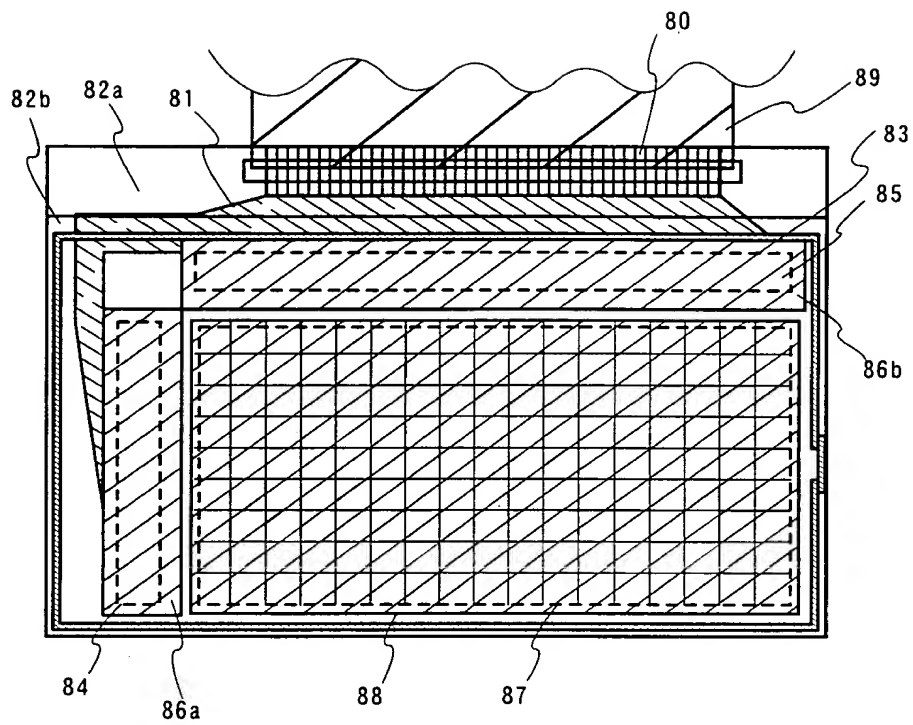


FIG. 8

09966639-092701

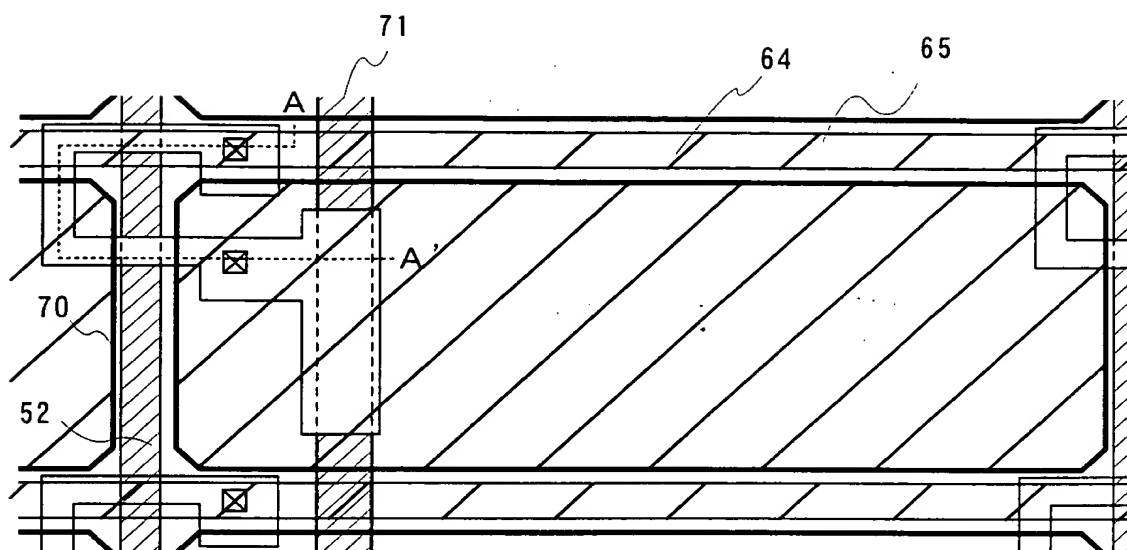


FIG. 9A

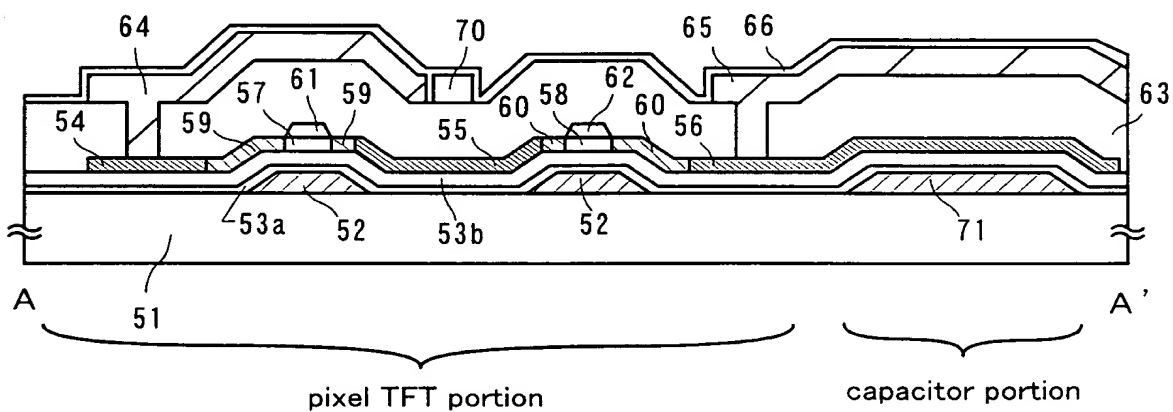


FIG. 9B

0966689-092701

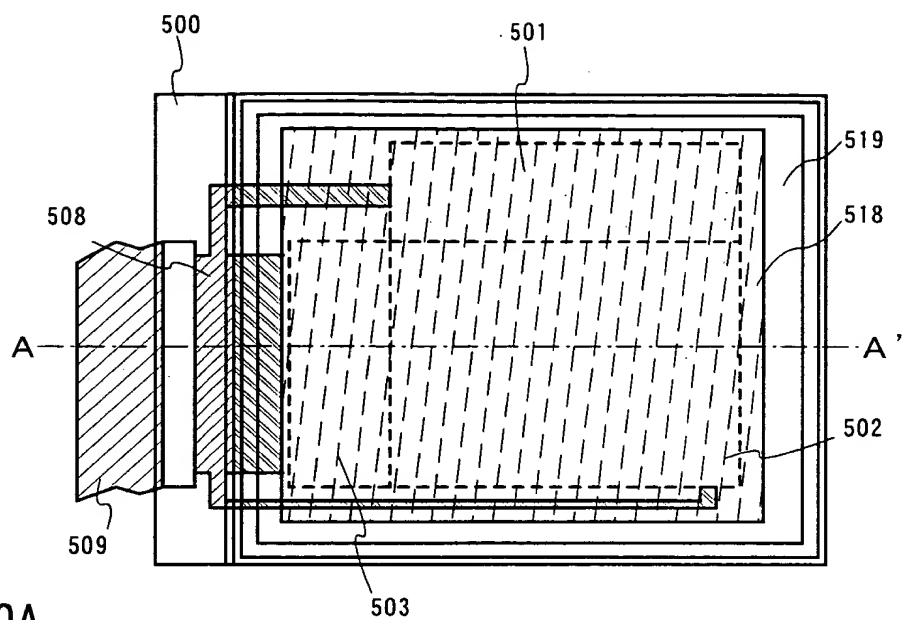


FIG. 10A

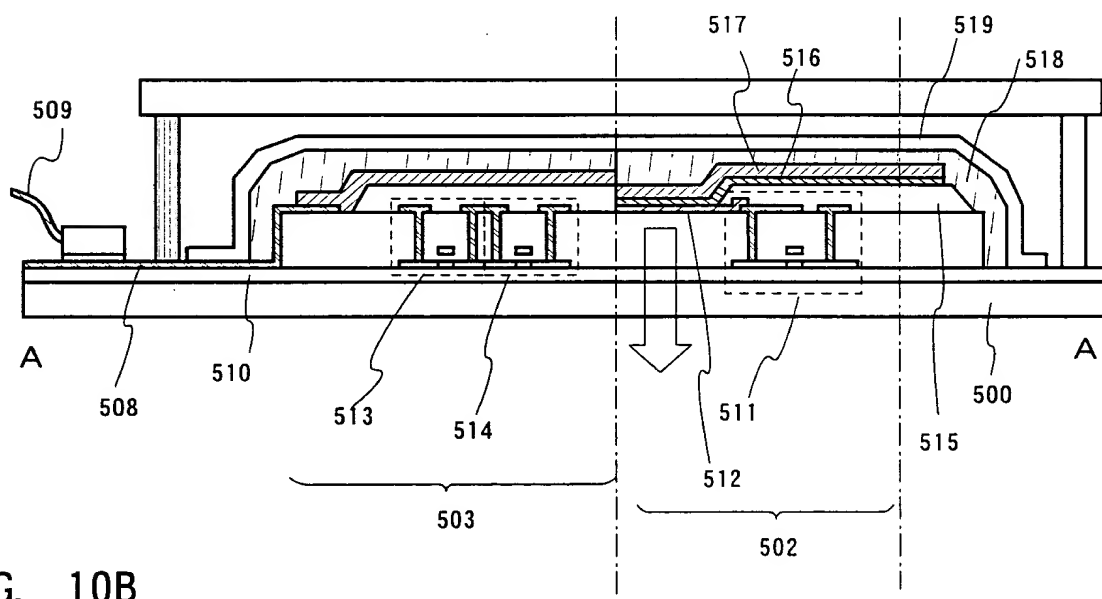


FIG. 10B

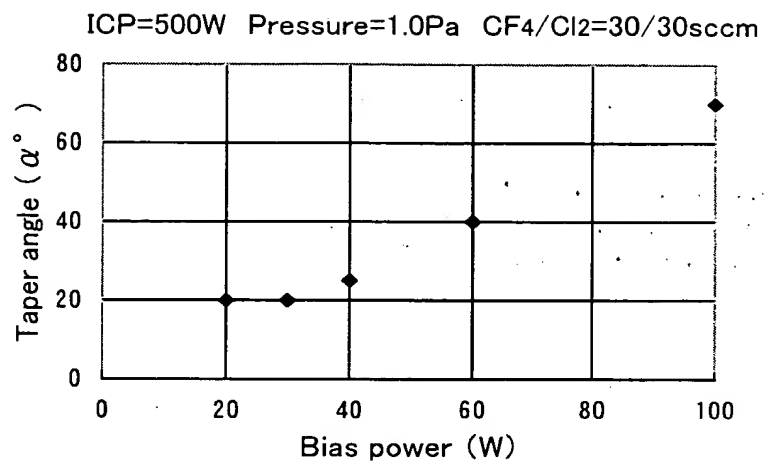


FIG. 11 Dependence of taper angle on bias power.

096689-0220

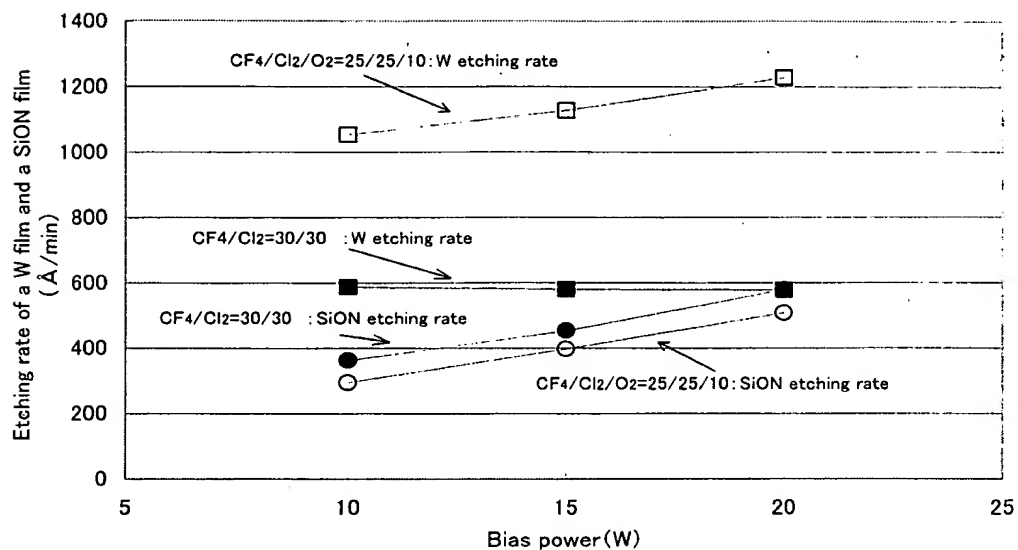


FIG. 12
Dependence of an etching rate of a W film and an SiON film on bias power.

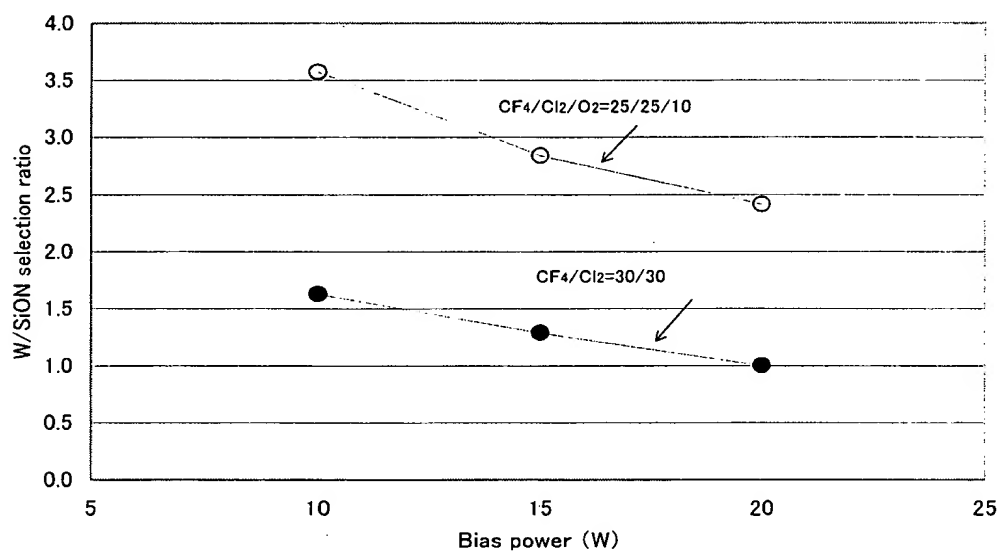


FIG. 13
Dependence of a selection ratio between a W film and an SiON film on a bias power.

0996689-092701

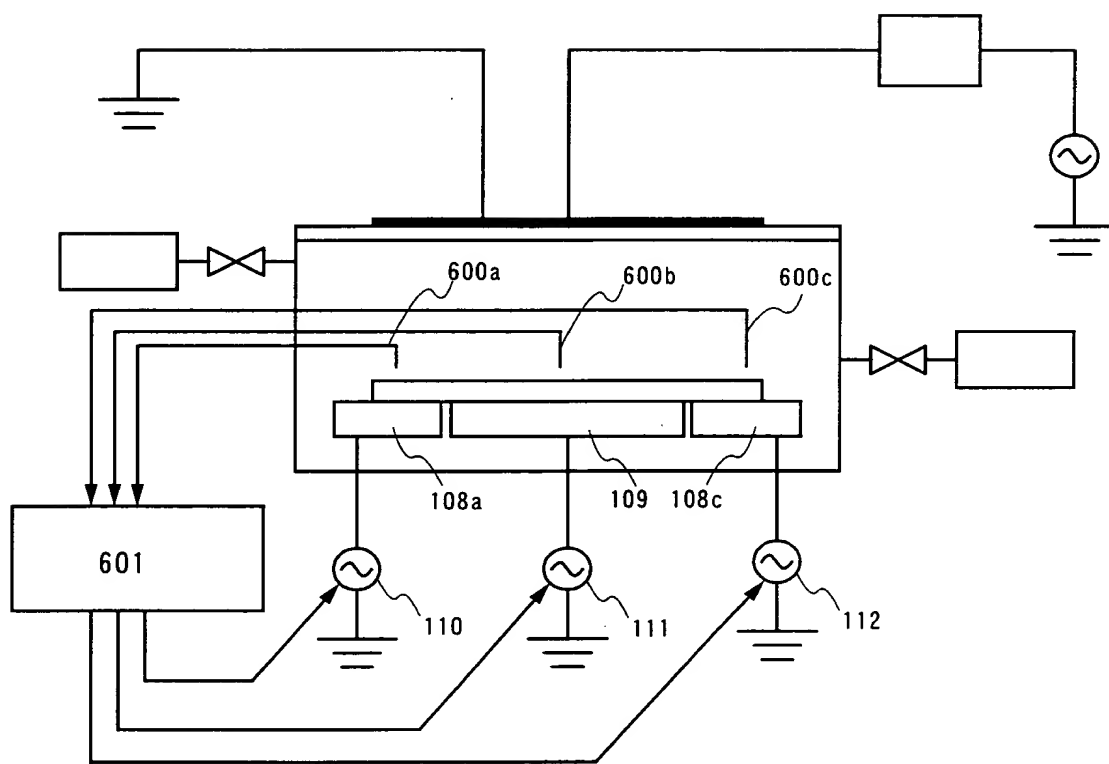


FIG. 14

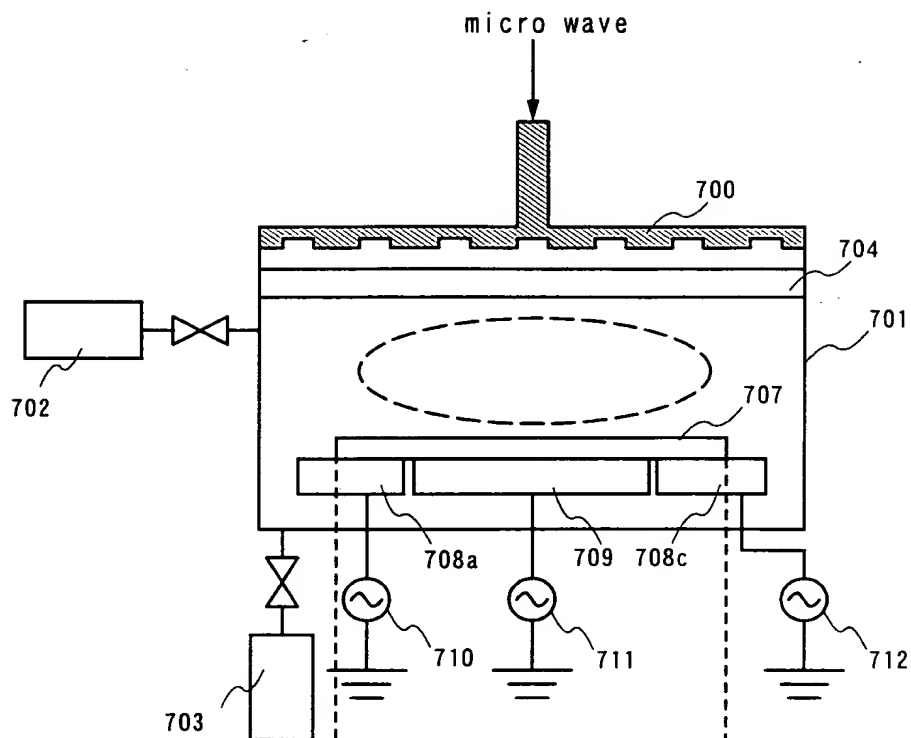


FIG. 15A

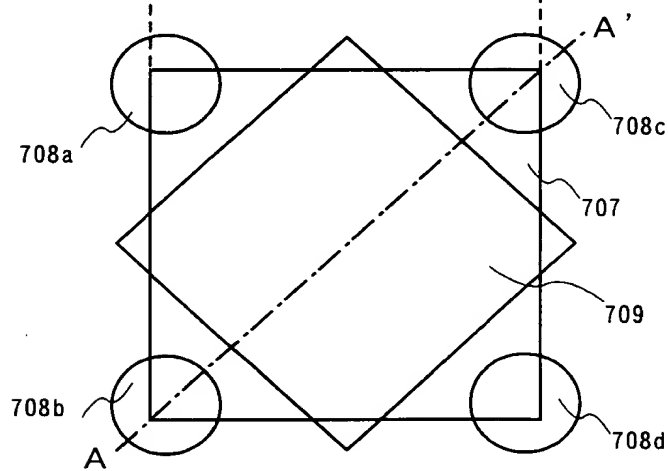


FIG. 15B

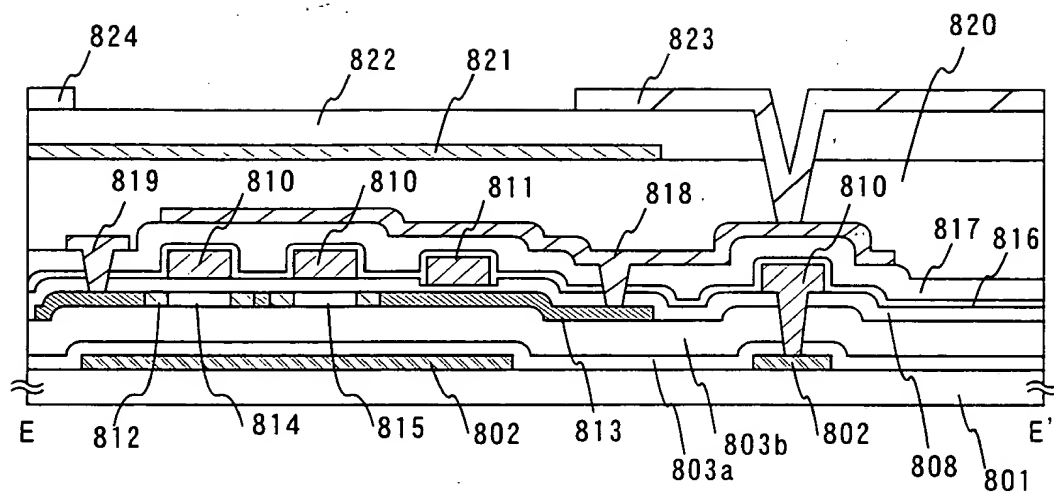


FIG. 16A

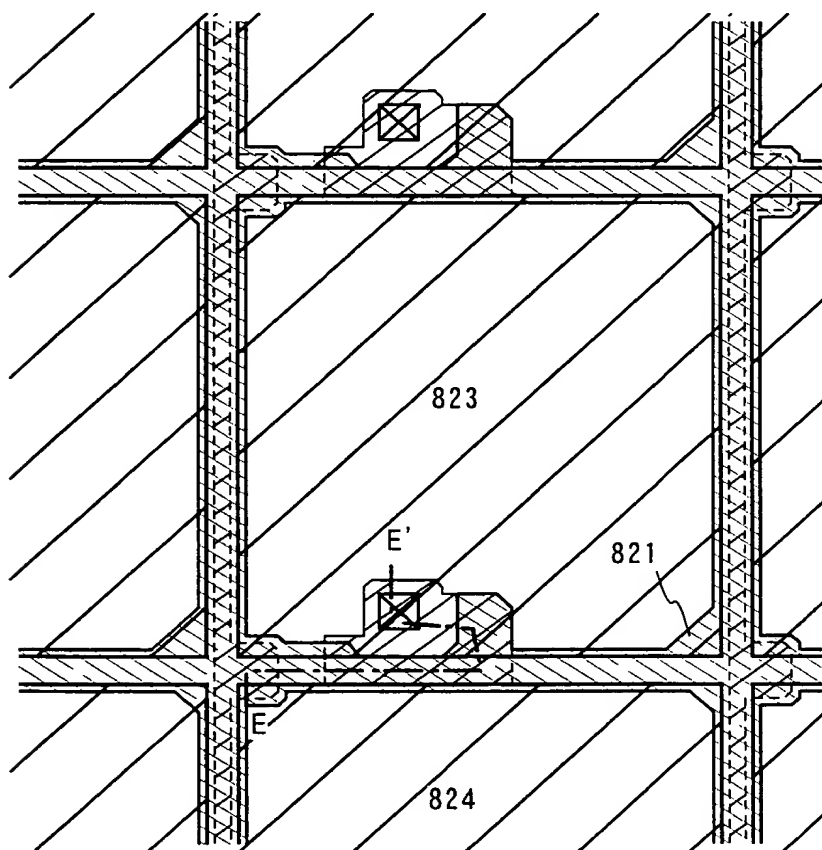


FIG. 16B

0966689-092701

09966689.092701

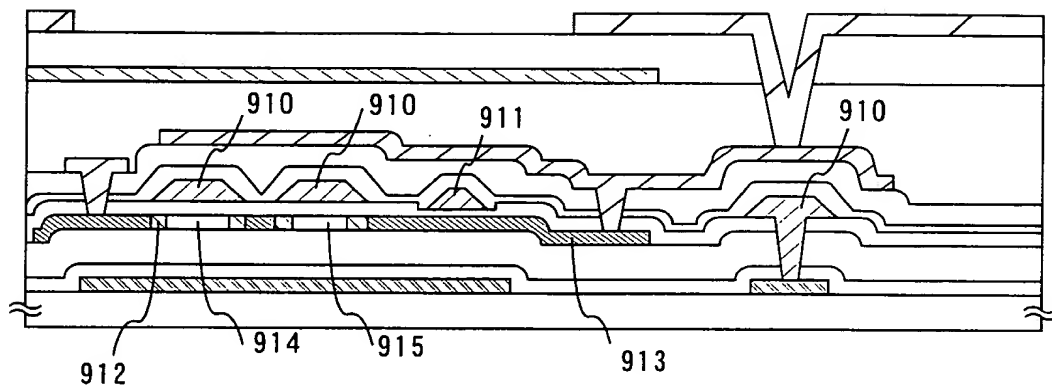


FIG. 17

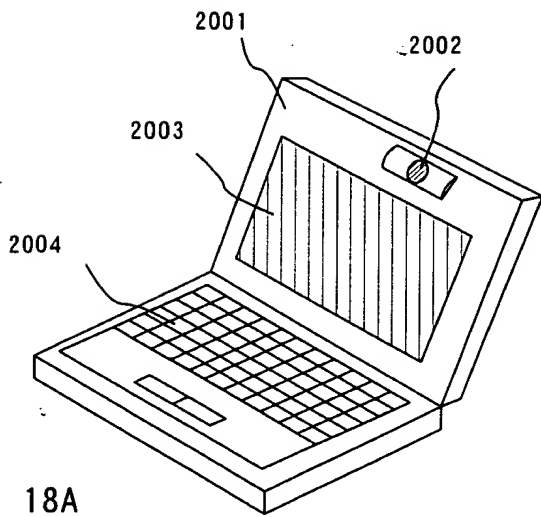


FIG. 18A

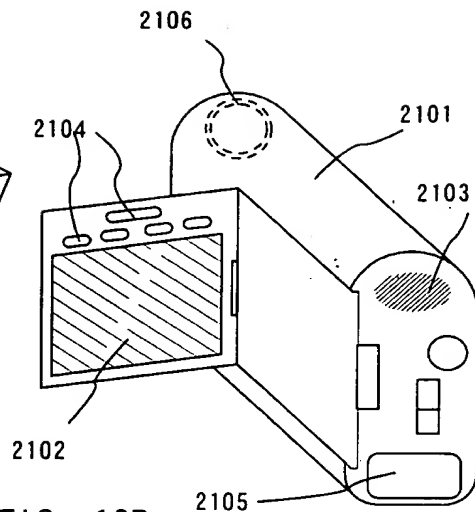


FIG. 18B

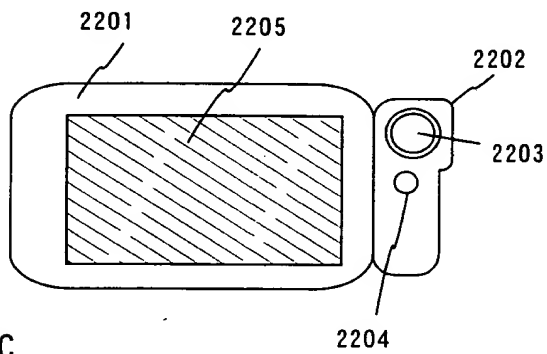


FIG. 18C

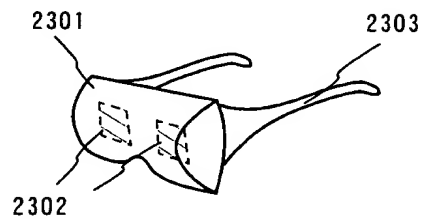


FIG. 18D

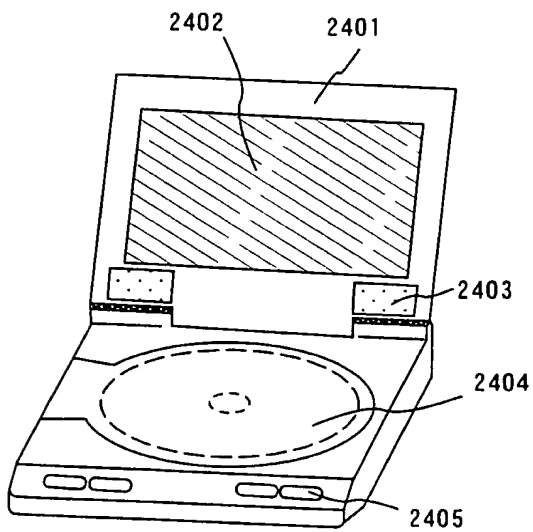


FIG. 18E

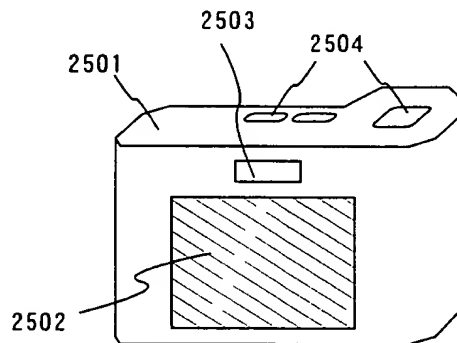


FIG. 18F

FIG. 18A-18F

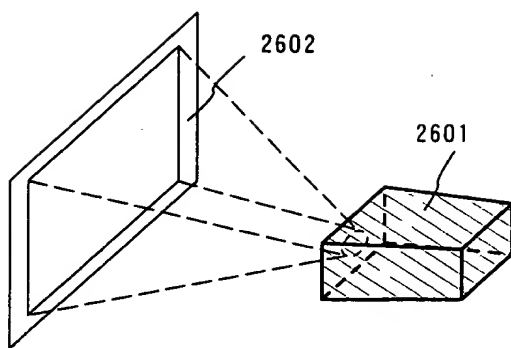


FIG. 19A

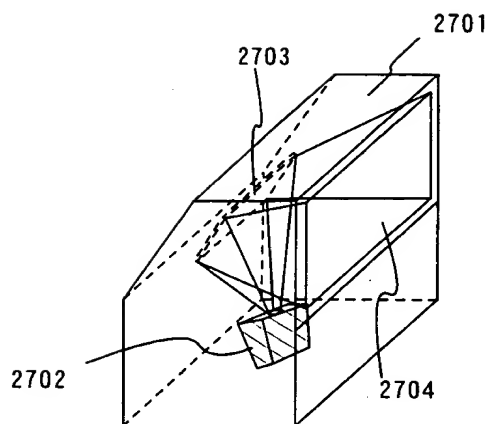


FIG. 19B

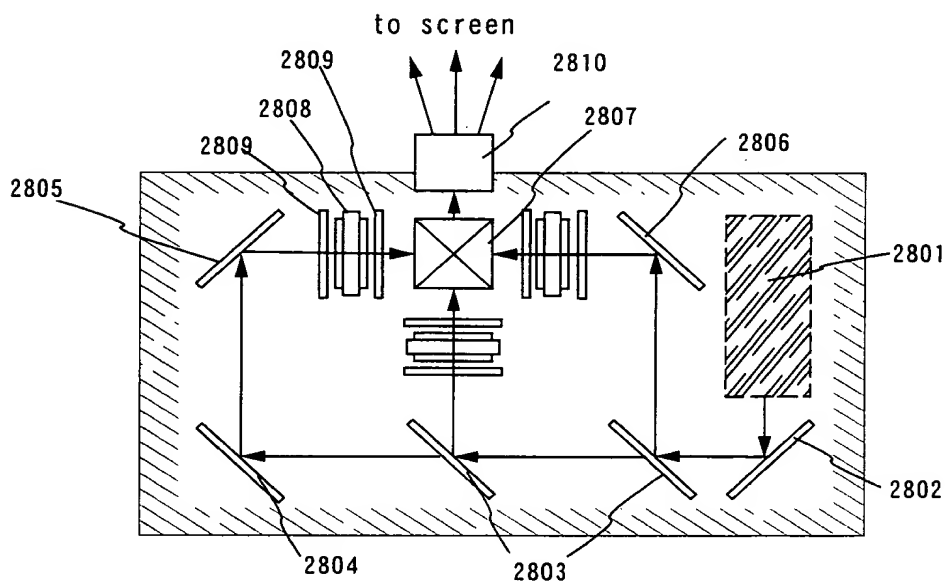


FIG. 19C

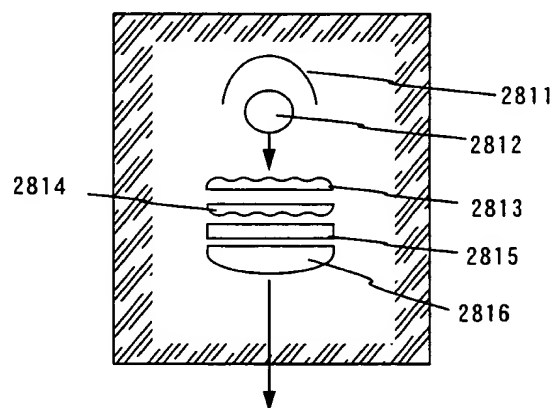


FIG. 19D

096689-092701

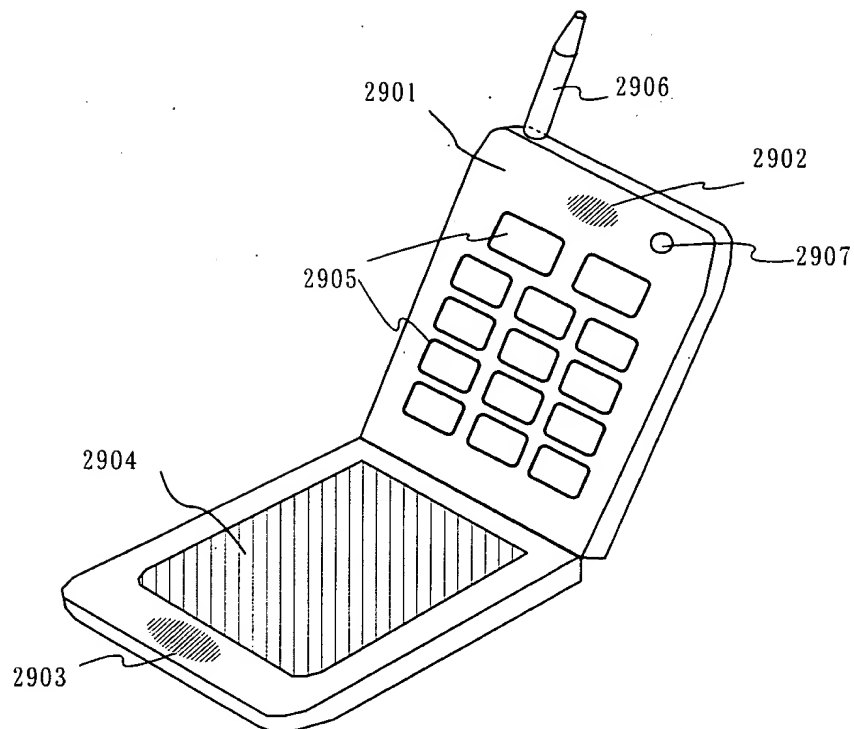


FIG. 20A

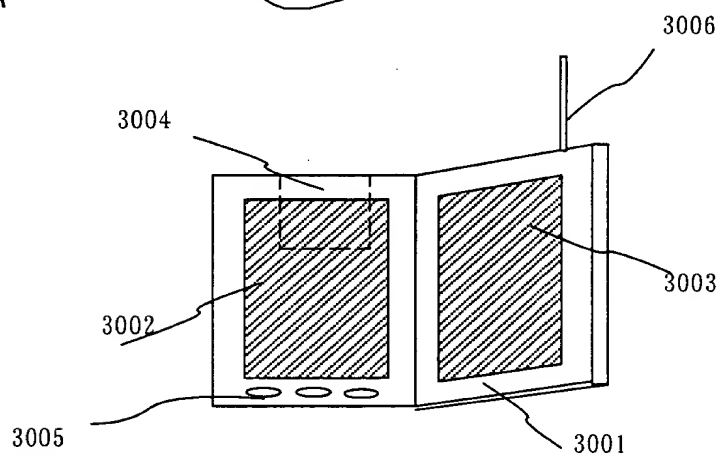


FIG. 20B

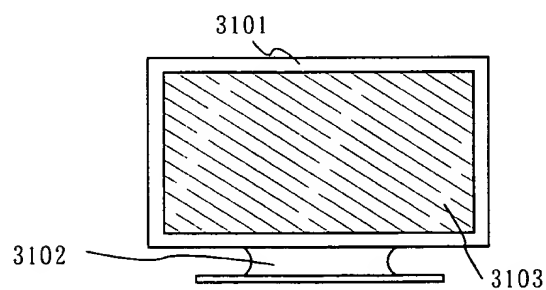


FIG. 20C

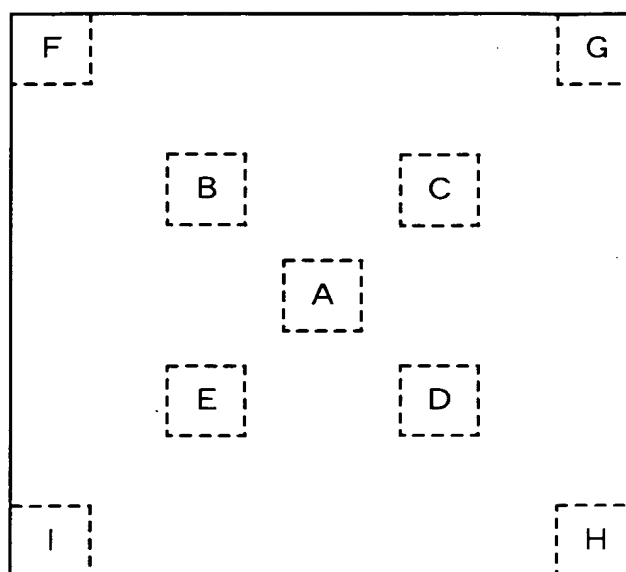


FIG. 21A

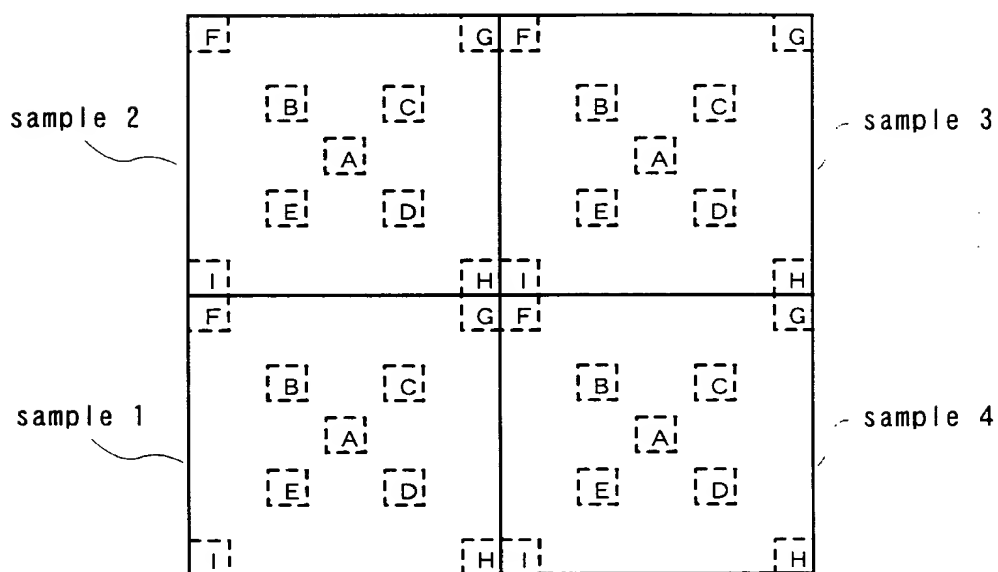


FIG. 21B